

LSF0102-Q1 汽车类 2 通道自动双向多电压电平转换器

1 特性

- 符合面向汽车应用的 AEC-Q100 应用
 - 温度等级 1: $-40^{\circ}\text{C} \leq T_A \leq 125^{\circ}\text{C}$
 - 器件 HBM ESD 分类等级 2
 - CDM ESD 分类等级 C6
- 用无方向引脚提供双向电压转换
- 支持漏极开路或推挽应用，如 I²C、SPI、UART、MDIO、SDIO 和 GPIO
- 容性负载
 - $\leq 30\text{pF}$ 时，最高支持 100MHz 的升压转换和 100MHz 以上的降压转换；容性负载为 50pF 时，最高支持 40MHz 的升压/降压转换
- 可实现以下电压之间的双向电压电平转换
 - $0.95\text{V} \leftrightarrow 1.8/2.5/3.3/5\text{V}$
 - $1.2\text{V} \leftrightarrow 1.8/2.5/3.3/5\text{V}$
 - $1.8\text{V} \leftrightarrow 2.5/3.3/5\text{V}$
 - $2.5\text{V} \leftrightarrow 3.3/5\text{V}$
 - $3.3\text{V} \leftrightarrow 5\text{V}$
- 低待机电流
- 5V 耐受 I/O 端口，可支持 TTL 电压电平
- 低导通电阻，可减少信号失真
- EN = 低电平时为高阻抗 I/O 引脚
- 采用直通引脚排列以简化 PCB 布线
- 锁断性能超过 100mA，符合 JESD 78 II 类规范的要求

2 应用

- 信息娱乐系统音响主机
- 图形群集
- ADAS 融合
- ADAS 前置摄像头
- HEV 电池管理系统

3 说明

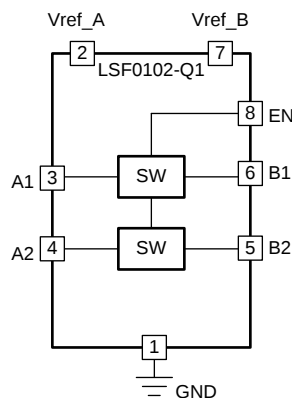
LSF0102-Q1 器件是一款自动双向电压转换器，无需方向引脚即可在广泛的电源范围内进行转换。当容性负载 $\leq 30\text{pF}$ 时，LSF0102-Q1 支持最高 100MHz 的升压转换和高于 100MHz 的降压转换。此外，当容性负载为 50pF 时，LSF0102-Q1 支持最高 40MHz 的升压和降压转换，因此，LSF0102-Q1 器件可支持汽车应用中各种常见的标准接口，如 I²C、SPI、GPIO、SDIO、UART 和 MDIO。

LSF0102-Q1 器件具有 5V 耐受数据输入。因此该器件可兼容 TTL 电压电平。此外，LSF0102-Q1 还支持混合模式电压转换，可在各个通道上升压和降压转换至不同的电源电平。

器件信息⁽¹⁾

器件型号	封装（引脚）	封装尺寸（标称值）
LSF0102QDCURQ1	超薄小外形尺寸封装 (VSSOP)(8)	2.30mm x 2.00mm

(1) 如需了解所有可用封装，请参阅数据表末尾的可订购产品附录。



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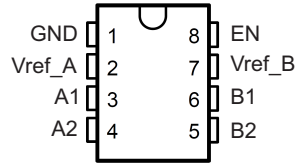
4 修订历史记录

注：之前版本的页码可能与当前版本有所不同。

日期	修订版本	说明
2018 年 5 月	*	最初发布版本。

5 Pin Configuration and Functions

**LSF0102-Q1 DCU Package
8-Pin VSSOP
Top View**



Pin Functions

PIN		I/O	DESCRIPTION
NAME	DCU		
A1	3	I/O	Input/Output A port for Channel 1
A2	4	I/O	Input/Output A port for Channel 2
B1	6	I/O	Input/Output B port for Channel 1
B2	5	I/O	Input/Output B port for Channel 2
EN	8	I	I/O enable input; see Figure 7 for typical setup. Should be tied directly to Vref_B to be enabled or pulled LOW to disable all I/O pins.
GND	1	—	Ground
Vref_A	2	—	A side reference supply voltage; see Application and Implementation for setup and supply voltage range.
Vref_B	7	—	B side reference supply voltage. Must be connected to supply through 200 kΩ; see Application and Implementation for setup and supply voltage range.

6 Specifications

6.1 Absolute Maximum Ratings

over operating free-air temperature (unless otherwise noted)⁽¹⁾

	MIN	MAX	UNIT
Input voltage ⁽²⁾ , V_I	–0.5	7	V
Input/output voltage ⁽²⁾ , $V_{I/O}$	–0.5	7	V
Continuous channel current		128	mA
Input clamp current, I_{IK}	$V_I < 0$	–50	mA
Storage temperature range, T_{stg}	–65	150	°C
Operating junction temperature, T_J		150	°C

- (1) Stresses beyond those listed under *Absolute Maximum Ratings* may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under *Recommended Operating Conditions* is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.
- (2) The input and input/output negative-voltage ratings may be exceeded if the input and input/output clamp-current ratings are observed.

6.2 ESD Ratings

	VALUE	UNIT
$V_{(ESD)}$ Electrostatic discharge	Human-body model (HBM), per AEC Q100-002 ⁽¹⁾	±2000
	Charged-device model (CDM), per AEC Q100-011	±1000
		V

- (1) AEC Q100-002 indicates that HBM stressing shall be in accordance with the ANSI/ESDA/JEDEC JS-001 specification.

6.3 Recommended Operating Conditions

over operating free-air temperature range (unless otherwise noted)

	MIN	MAX	UNIT
$V_{I/O}$ Input/output voltage		5	V
$V_{ref_A/B/EN}$ Reference voltage		5	V
I_{PASS} Pass transistor current		64	mA
T_A Operating free-air temperature	–40	125	°C

6.4 Thermal Information

THERMAL METRIC ⁽¹⁾	LSF0102-Q1	UNIT
	DCU (US8)	
	8 PINS	
$R_{\theta JA}$ Junction-to-ambient thermal resistance	229.3	°C/W
$R_{\theta JC(top)}$ Junction-to-case (top) thermal resistance	106.5	°C/W
$R_{\theta JB}$ Junction-to-board thermal resistance	141.7	°C/W
Ψ_{JT} Junction-to-top characterization parameter	35.3	°C/W
Ψ_{JB} Junction-to-board characterization parameter	141.4	°C/W

- (1) For more information about traditional and new thermal metrics, see the [IC Package Thermal Metrics](#) application report.

6.5 Electrical Characteristics

over recommended operating free-air temperature range (unless otherwise noted)

PARAMETER		TEST CONDITIONS	MIN	TYP ⁽¹⁾	MAX	UNIT
V_{IK}	Input clamp voltage	$I_I = -18 \text{ mA}$, $V_{EN} = 0$			-1.2	V
I_{IH}	I/O input high leakage	$V_I = 5 \text{ V}$, $V_{EN} = 0$			5.0	μA
I_{CCBA}	V_{ref_B} to V_{ref_A} leakage	$V_{ref_B} = V_{EN} = 5.5 \text{ V}$, $V_{ref_A} = 4.5 \text{ V}$, $I_O = 0$, $V_I = V_{CC}$ or GND		1		μA
$C_{I(ref_A/B/EN)}$	Input capacitance	$V_I = 3 \text{ V}$ or 0		11		pF
$C_{io(off)}$	I/O pin off-state capacitance	$V_O = 3 \text{ V}$ or 0, $V_{EN} = 0$		4.0	6.0	pF
$C_{io(on)}$	I/O Pin on-state capacitance	$V_O = 3 \text{ V}$ or 0, $V_{EN} = 3 \text{ V}$		10.5	12.5	pF
$r_{on}^{(2)}$	On-state resistance	$V_I = 0$, $I_O = 64 \text{ mA}$	$V_{ref_A} = 3.3 \text{ V}$; $V_{ref_B} = V_{EN} = 5 \text{ V}$		8.0	Ω
			$V_{ref_A} = 1.8 \text{ V}$; $V_{ref_B} = V_{EN} = 5 \text{ V}$		9.0	
			$V_{ref_A} = 1.0 \text{ V}$; $V_{ref_B} = V_{EN} = 5 \text{ V}$		10	
		$V_I = 0$, $I_O = 32 \text{ mA}$	$V_{ref_A} = 1.8 \text{ V}$; $V_{ref_B} = V_{EN} = 5 \text{ V}$		10	Ω
			$V_{ref_A} = 2.5 \text{ V}$; $V_{ref_B} = V_{EN} = 5 \text{ V}$		15	
		$V_I = 1.8 \text{ V}$, $I_O = 15 \text{ mA}$	$V_{ref_A} = 3.3 \text{ V}$; $V_{ref_B} = V_{EN} = 5 \text{ V}$		9.0	Ω
		$V_I = 1.0 \text{ V}$, $I_O = 10 \text{ mA}$	$V_{ref_A} = 1.8 \text{ V}$; $V_{ref_B} = V_{EN} = 3.3 \text{ V}$		18	Ω
		$V_I = 0 \text{ V}$, $I_O = 10 \text{ mA}$	$V_{ref_A} = 1.0 \text{ V}$; $V_{ref_B} = V_{EN} = 3.3 \text{ V}$		20	Ω
		$V_I = 0 \text{ V}$, $I_O = 10 \text{ mA}$	$V_{ref_A} = 1.0 \text{ V}$; $V_{ref_B} = V_{EN} = 1.8 \text{ V}$		30	Ω

(1) All typical values are at $T_A = 25^\circ\text{C}$.

(2) Measured by the voltage drop between the A and B pins at the indicated current through the switch. On-state resistance is determined by the lowest voltage of the two (A or B) pins.

6.6 Switching Characteristics (Translating Down): $V_{GATE} = 3.3\text{ V}$

over recommended operating free-air temperature range, $V_{GATE} = 3.3\text{ V}$, $V_{IH} = 3.3\text{ V}$, $V_{IL} = 0$, and $V_M = 1.15\text{ V}$ (unless otherwise noted) (see [Parameter Measurement Information](#) table)

PARAMETER	TEST CONDITIONS	$C_L = 50\text{ pF}$			$C_L = 30\text{ pF}$			$C_L = 15\text{ pF}$			UNIT
		MIN	TYP	MAX	MIN	TYP	MAX	MIN	TYP	MAX	
t_{PLH}	Propagation delay time, low-to-high output		1.1			0.7			0.3		ns
t_{PHL}	Propagation delay time, high-to-low output		1.2			0.8			0.4		

6.7 Switching Characteristics (Translating Down): $V_{GATE} = 2.5\text{ V}$

over recommended operating free-air temperature range, $V_{GATE} = 2.5\text{ V}$, $V_{IH} = 2.5\text{ V}$, $V_{IL} = 0$, and $V_M = 0.75\text{ V}$ (unless otherwise noted) (see [Parameter Measurement Information](#) table)

PARAMETER	TEST CONDITIONS	$C_L = 50\text{ pF}$			$C_L = 30\text{ pF}$			$C_L = 15\text{ pF}$			UNIT
		MIN	TYP	MAX	MIN	TYP	MAX	MIN	TYP	MAX	
t_{PLH}	Propagation delay time, low-to-high output		1.2			0.8			0.35		ns
t_{PHL}	Propagation delay time, high-to-low output		1.3			1			0.5		

6.8 Switching Characteristics Translating Up): $V_{GATE} = 3.3\text{ V}$

over recommended operating free-air temperature range, $V_{GATE} = 3.3\text{ V}$, $V_{IH} = 2.3\text{ V}$, $V_{IL} = 0$, $V_T = 3.3\text{ V}$, $V_M = 1.15\text{ V}$ and $R_L = 300$ (unless otherwise noted) (see [Parameter Measurement Information](#) table)

PARAMETER	TEST CONDITIONS	$C_L = 50\text{ pF}$			$C_L = 30\text{ pF}$			$C_L = 15\text{ pF}$			UNIT
		MIN	TYP	MAX	MIN	TYP	MAX	MIN	TYP	MAX	
t_{PLH}	Propagation delay time, low-to-high output		1			0.8			0.4		ns
t_{PHL}	Propagation delay time, high-to-low output		1			0.9			0.4		

6.9 Switching Characteristics (Translating Up): $V_{GATE} = 2.5\text{ V}$

over recommended operating free-air temperature range, $V_{GATE} = 2.5\text{ V}$, $V_{IH} = 1.5\text{ V}$, $V_{IL} = 0$, $V_T = 2.5\text{ V}$, $V_M = 0.75\text{ V}$ and $R_L = 300$ (unless otherwise noted) (see [Parameter Measurement Information](#) table)

PARAMETER	TEST CONDITIONS	$C_L = 50\text{ pF}$			$C_L = 30\text{ pF}$			$C_L = 15\text{ pF}$			UNIT
		MIN	TYP	MAX	MIN	TYP	MAX	MIN	TYP	MAX	
t_{PLH}	Propagation delay time, low-to-high output		1.1			0.9			0.45		ns
t_{PHL}	Propagation delay time, high-to-low output		1.3			1.1			0.6		

6.10 Typical Characteristics

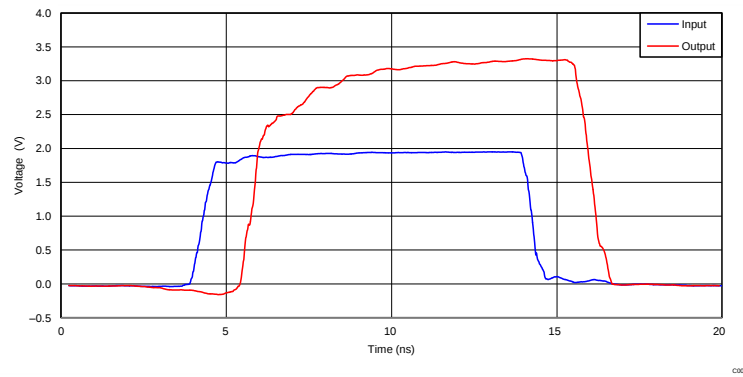
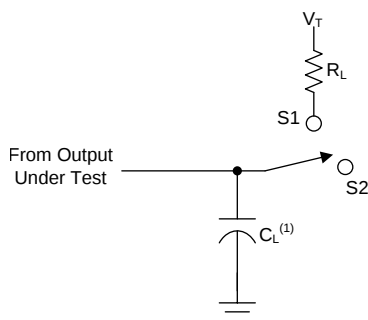


图 1. Signal Integrity (1.8 to 3.3 V Translation Up at 50 MHz)

7 Parameter Measurement Information

The outputs are measured one at a time, with one transition per measurement. All input pulses are supplied by generators that have the following characteristics:

- $PRR \leq 10 \text{ MHz}$
- $Z_O = 50 \Omega$
- $t_r \leq 2 \text{ ns}$
- $t_f \leq 2 \text{ ns}$



(1) C_L includes probe and jig capacitance.

图 2. Load Circuit

USAGE	SWITCH
Translating Up	S1
Translating Down	S2

图 3. Translating Up and Down Table

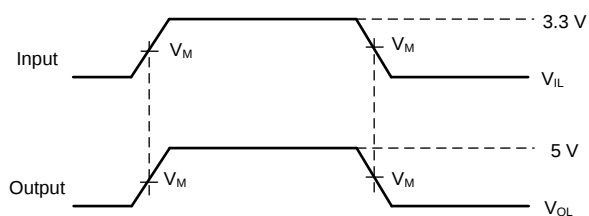


图 4. Translating Up

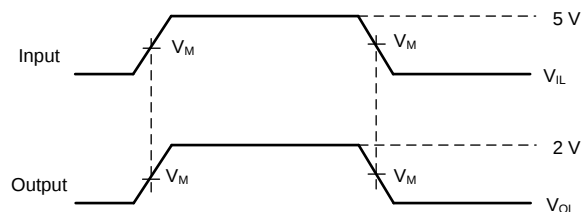


图 5. Translating Down

8 Detailed Description

8.1 Overview

The LSF0102-Q1 device can be used in level translation applications for interfacing devices or systems operating at different interface voltages. The LSF0102-Q1 device is ideal for use in applications where an open-drain driver is connected to the data I/Os. With appropriate pull-up resistors and layout, the LSF0102-Q1 device can achieve 100 MHz. The LSF0102-Q1 can also be used in applications where a push-pull driver is connected to the data I/Os.

8.2 Functional Block Diagrams

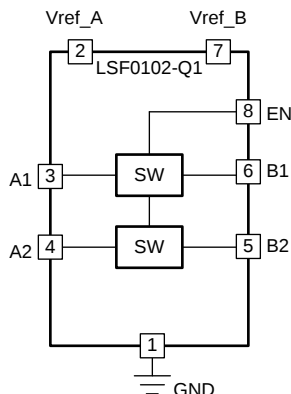


图 6. LSF0102-Q1 Functional Block Diagram

8.3 Feature Description

8.3.1 Auto Bidirectional Voltage Translation

The LSF0102-Q1 device is an auto bidirectional voltage level translator that operates from 0.95 to 4.5 V on Vref_A and 1.8 to 5.5 V on Vref_B. This allows bidirectional voltage translation between 0.95 V and 5.5 V without the need for a direction pin in open-drain or push-pull applications. The LSF0102-Q1 device supports level translation applications with transmission speeds greater than 100 Mbps for open-drain systems using a 250-Ω pullup resistor with a 30-pF capacitive load.

8.3.2 Output Enable

When EN is HIGH, the translator switch is on, and the An I/O is connected to the Bn I/O, respectively, allowing bidirectional data flow between ports. When EN is LOW, the translator switch is off, and a high-impedance state exists between ports. To enable the I/O pins, the EN input should be tied directly to Vref_B. To ensure the high-impedance state during power-up or power-down, EN must be LOW. For additional details on how to use the enable pin, see the [Using the Enable Pin with the LSF Family](#) video.

表 1. Enable Function Table

INPUT EN ⁽¹⁾ PIN	FUNCTION
Tied directly to Vref_B	An = Bn
L	Hi-Z

(1) EN is controlled by Vref_B logic levels and should be at least 1 V higher than Vref_A for best translator.

8.3.3 Mixed-Mode Voltage Translation

The supply voltage (Vpu#) for each channel can be individually set up with a pull-up resistor. For example, CH1 can be used in up-translation mode (1.2 V ↔ 3.3 V) and CH2 in down-translation mode (2.5 V ↔ 1.8 V). For additional details on how to use the LSF0102-Q1 for mixed-mode voltage translation, see the [Multi-Voltage Translation with the LSF Family](#) video.

8.4 Device Functional Modes

When the An or Bn port is LOW, the switch is in the ON-state and a low resistance connection exists between the An and Bn ports. The low R_{on} of the switch allows connections to be made with minimal propagation delay and signal distortion. Assuming the higher voltage is on the Bn port when the Bn port is HIGH, the voltage on the An port is limited to the voltage set by Vref_A. When the An port is HIGH, the Bn port is pulled to the drain pull-up supply voltage ($V_{pu\#}$) by the pull-up resistors. This functionality allows a seamless translation between higher and lower voltages selected by the user without the need for direction control. For additional details on the functional operation of the LSF0102-Q1, see the [Down Translation with the LSF Family](#) and [Up Translation with the LSF Family](#) videos.

9 Application and Implementation

注

Information in the following applications sections is not part of the TI component specification, and TI does not warrant its accuracy or completeness. TI's customers are responsible for determining suitability of components for their purposes. Customers should validate and test their design implementation to confirm system functionality.

9.1 Application Information

The LSF0102-Q1 device is able to perform voltage translation for open-drain or push-pull interfaces such as I²C, SPI, UART, MDIO, SDIO, and GPIO.

9.2 Typical Application

9.2.1 Bidirectional Translation

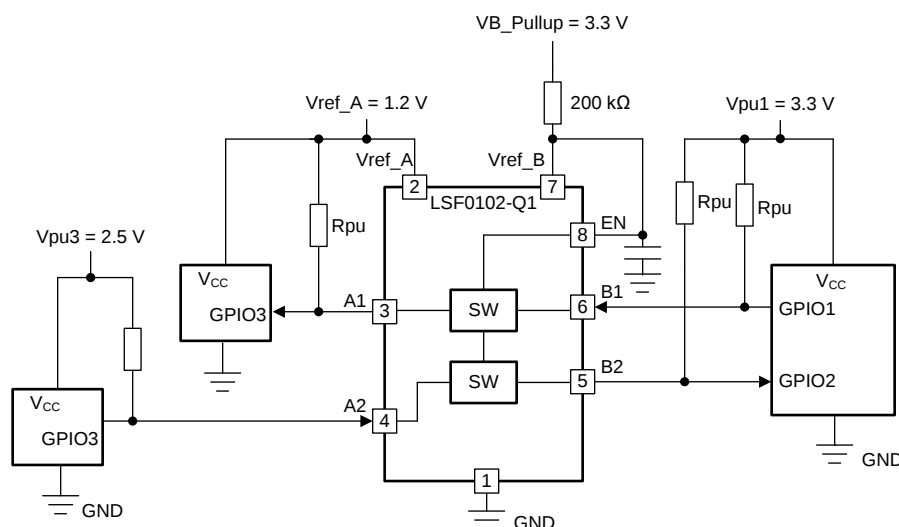


图 7. Bidirectional Translation to Multiple Voltage Levels

9.2.1.1 Design Requirements

9.2.1.1.1 Enable, Disable, and Reference Voltage Guidelines

The LSF0102-Q1 device has an EN input that is used to disable the device by setting EN LOW, which places all I/Os in the high-impedance state. Since LSF family is switch-type voltage translator, the power consumption is very low. It is recommended to always enable LSF0102-Q1 device for bidirectional applications by connecting the EN pin to the Vref_B pin, as shown in 图 7. For additional details on setting up the Vref_A, Vref_B, and EN pins, see the [Understanding the Bias Circuit for the LSF Family](#) video.

Typical Application (接下页)

表 2. Application Operating Condition

PARAMETER		MIN	TYP	MAX	UNIT
Vref_A ⁽¹⁾	reference voltage (A)	0.95		4.5	V
Vref_B	reference voltage (B)	Vref_A + 0.8		5.5	V
V _{I(EN)}	input voltage on EN pin	Vref_A + 0.8	Vref_B	5.5	V
V _{pu}	pull-up supply voltage	0		Vref_B	V

(1) Vref_A is required to be the lowest voltage level across all inputs and outputs.

The 200 kΩ, pull-up resistor is required to allow Vref_B to regulate the EN input. A filter capacitor on Vref_B is recommended. Also Vref_B and V_{I(EN)} are recommended to be 1.0 V higher than Vref_A for best signal integrity.

9.2.1.2 Detailed Design Procedure

9.2.1.2.1 Bidirectional Translation

For the bidirectional clamping configuration (higher voltage to lower voltage or lower voltage to higher voltage), the EN input must be connected to Vref_B and both pins pulled to HIGH side V_{pu} through a pull-up resistor (typically 200 kΩ), as shown in [图 7](#). This allows Vref_B to regulate the EN input. A filter capacitor on Vref_B is recommended. The master output driver can be push-pull or open-drain (pull-up resistors may be required) and the slave device output can be push-pull or open-drain (pull-up resistors are required to pull the Bn outputs to V_{pu}).

If either output is push-pull, data must be unidirectional or the outputs must be tri-state and be controlled by some direction-control mechanism to prevent HIGH-to-LOW contention in either direction. If both outputs are open-drain, no direction control is needed.

In [图 7](#), the reference supply voltage (Vref_A) is connected to the processor core power supply voltage. When Vref_B is connected through a 200 kΩ resistor to a 3.3 V V_{pu} power supply, and Vref_A is set 1.2 V. The output of A1 has a maximum output voltage equal to Vref_A, and the bidirectional interface on channel 2 has a maximum output voltage equal to V_{pu}.

9.2.1.2.2 Pull-up Resistor Sizing

To maintain an appropriate output low voltage, the pull-up resistor value should limit the current through the pass transistor when it is in the ON state to less than 15 mA. This ensures a pass voltage of 260 mV to 350 mV. To set the current through each pass transistor at 15 mA, the pull-up resistor value can be calculated using the following equation:

$$R_{pu} = (V_{pu} - 0.35 \text{ V}) / 0.015 \text{ A} \quad (1)$$

The appropriate pull up resistor will depend on the current requirements of the application. [表 3](#) summarizes resistor values, reference voltages, and currents at 15 mA, 10 mA, and 3 mA. The resistor value shown in the +10% column (or a larger value) should be used to ensure that the pass voltage of the transistor is 350 mV or less. The external driver must be able to sink the total current from the resistors on both sides of the LSF0102-Q1 device at 0.175 V, although the 15 mA applies only to current flowing through the LSF0102-Q1.

表 3. Pull-up Resistor Values⁽¹⁾⁽²⁾

V _{DPU}	15 mA		10 mA		3 mA	
	NOMINAL (Ω)	+10% ⁽³⁾ (Ω)	NOMINAL (Ω)	+10% ⁽³⁾ (Ω)	NOMINAL (Ω)	+10% ⁽³⁾ (Ω)
5 V	310	341	465	512	1550	1705
3.3 V	197	217	295	325	983	1082
2.5 V	143	158	215	237	717	788
1.8 V	97	106	145	160	483	532
1.5 V	77	85	115	127	383	422
1.2 V	57	63	85	94	283	312

(1) Calculated for V_{OL} = 0.35 V

(2) Assumes output driver V_{OL} = 0.175 V at stated current

(3) +10% to compensate for V_{DD} range and resistor tolerance

9.2.1.3 Application Curve

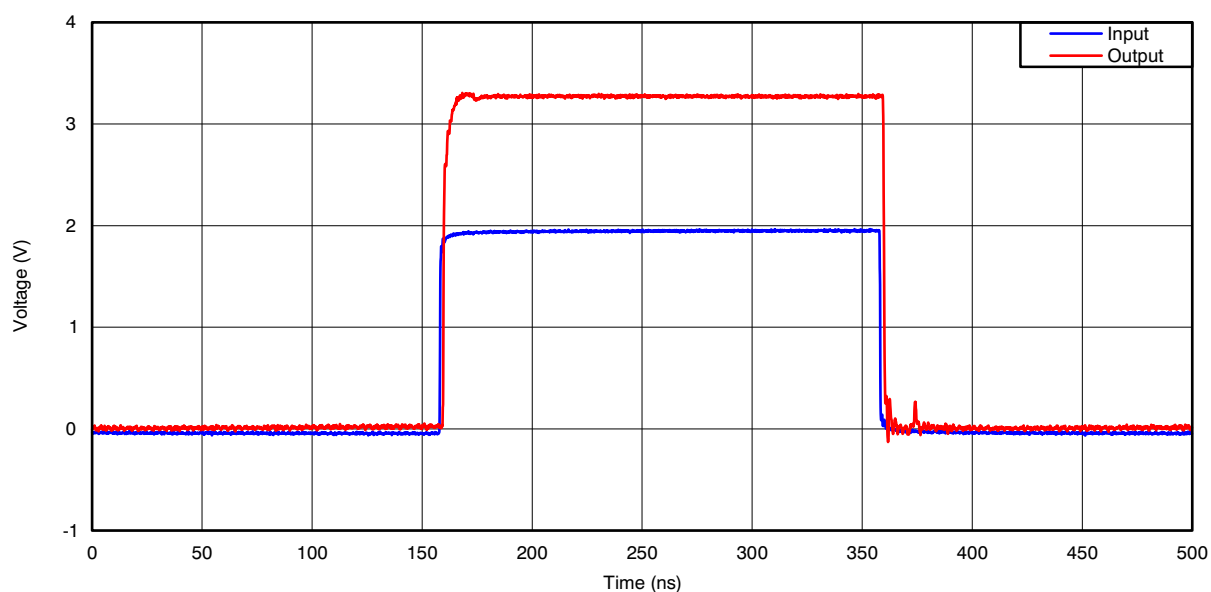


图 8. Captured Waveform From Above I²C Set-Up (1.8 V to 3.3 V at 2.5 MHz)

10 Power Supply Recommendations

There are no power sequence requirements for the LSF family. For recommended operating voltages for all supply and input pins, see [Table 5](#).

表 4. Recommended Operating Voltages

PARAMETER	MIN	TYP	MAX	UNIT
Vref_A ⁽¹⁾ reference voltage (A)	0.95		4.5	V
Vref_B reference voltage (B)	Vref_A + 0.8		5.5	V
V _{I(EN)} input voltage on EN pin	Vref_A + 0.8		5.5	V
V _{pu} pull-up supply voltage	0		Vref_B	V

(1) Vref_A is required to be the lowest voltage level across all inputs and outputs.

11 Layout

11.1 Layout Guidelines

Because the LSF0102-Q1 device is a switch-type level translator, the signal integrity is dependent upon the pull-up resistor value and PCB board parasitics. Consider the following recommendations when designing with the LSF0102-Q1.

- Minimize the signal trace length to reduce capacitance
- Avoid using stubs in the signal path to reduce parasitics.
- Place the LSF0102-Q1 device near the high voltage side.
- Select the appropriate pull-up resistor that applies to translation levels and driving capability of transmitter.

11.2 Layout Example

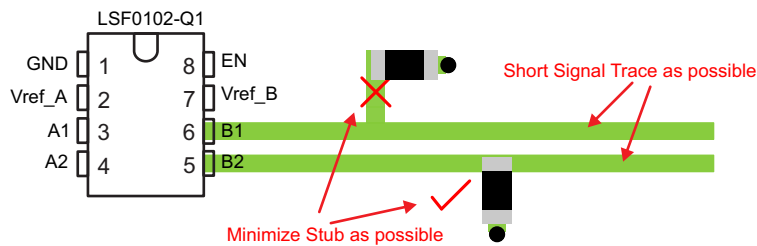


图 9. Short Trace Layout

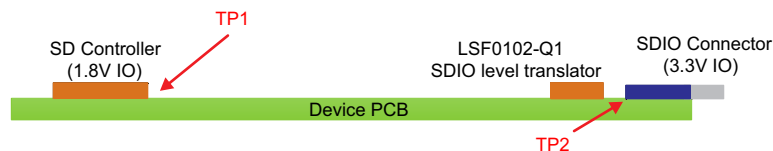


图 10. Device Placement

12 器件和文档支持

12.1 文档支持

12.1.1 相关文档

请参阅如下相关文档：

- 德州仪器 (TI), [TI Logic Minute: 《简介 – 使用 LSF 系列进行电压电平转换》](#) 视频
- 德州仪器 (TI), [《使用 LSF 系列进行电压电平转换》](#) 应用报告

12.2 相关链接

下表列出了快速访问链接。类别包括技术文档、支持与社区资源、工具和软件，以及申请样片或购买产品的快速链接。

表 5. 相关链接

器件	产品文件夹	样片与购买	技术文档	工具与软件	支持和社区
LSF0102	请单击此处	请单击此处	请单击此处	请单击此处	请单击此处

12.3 社区资源

下列链接提供到 TI 社区资源的连接。链接的内容由各个分销商“按照原样”提供。这些内容并不构成 TI 技术规范，并且不一定反映 TI 的观点；请参阅 TI 的 [《使用条款》](#)。

TI E2E™ 在线社区 *TI 的工程师对工程师 (E2E) 社区*。此社区的创建目的在于促进工程师之间的协作。在 e2e.ti.com 中，您可以咨询问题、分享知识、拓展思路并与同行工程师一道帮助解决问题。

设计支持 *TI 参考设计支持* 可帮助您快速查找有帮助的 E2E 论坛、设计支持工具以及技术支持的联系信息。

12.4 商标

E2E is a trademark of Texas Instruments.

12.5 静电放电警告



这些装置包含有限的内置 ESD 保护。存储或装卸时，应将导线一起截短或将装置放置于导电泡棉中，以防止 MOS 门极遭受静电损伤。

12.6 术语表

SLYZ022 — *TI 术语表*。

这份术语表列出并解释术语、缩写和定义。

13 机械、封装和可订购信息

以下页面包含机械、封装和可订购信息。这些信息是指定器件的最新可用数据。数据如有变更，恕不另行通知，且不会对此文档进行修订。如需获取此数据表的浏览器版本，请查阅左侧的导航栏。

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PACKAGING INFORMATION

Orderable Device	Status (1)	Package Type	Package Drawing	Pins	Package Qty	Eco Plan (2)	Lead finish/ Ball material (6)	MSL Peak Temp (3)	Op Temp (°C)	Device Marking (4/5)	Samples
LSF0102QDCURQ1	ACTIVE	VSSOP	DCU	8	3000	RoHS & Green	NIPDAUAG	Level-2-260C-1 YEAR	-40 to 125	NG2SQ	Samples

(1) The marketing status values are defined as follows:

ACTIVE: Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

OBSOLETE: TI has discontinued the production of the device.

(2) **RoHS:** TI defines "RoHS" to mean semiconductor products that are compliant with the current EU RoHS requirements for all 10 RoHS substances, including the requirement that RoHS substance do not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, "RoHS" products are suitable for use in specified lead-free processes. TI may reference these types of products as "Pb-Free".

RoHS Exempt: TI defines "RoHS Exempt" to mean products that contain lead but are compliant with EU RoHS pursuant to a specific EU RoHS exemption.

Green: TI defines "Green" to mean the content of Chlorine (Cl) and Bromine (Br) based flame retardants meet JS709B low halogen requirements of <=1000ppm threshold. Antimony trioxide based flame retardants must also meet the <=1000ppm threshold requirement.

(3) MSL, Peak Temp. - The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

(4) There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.

(5) Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "-" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.

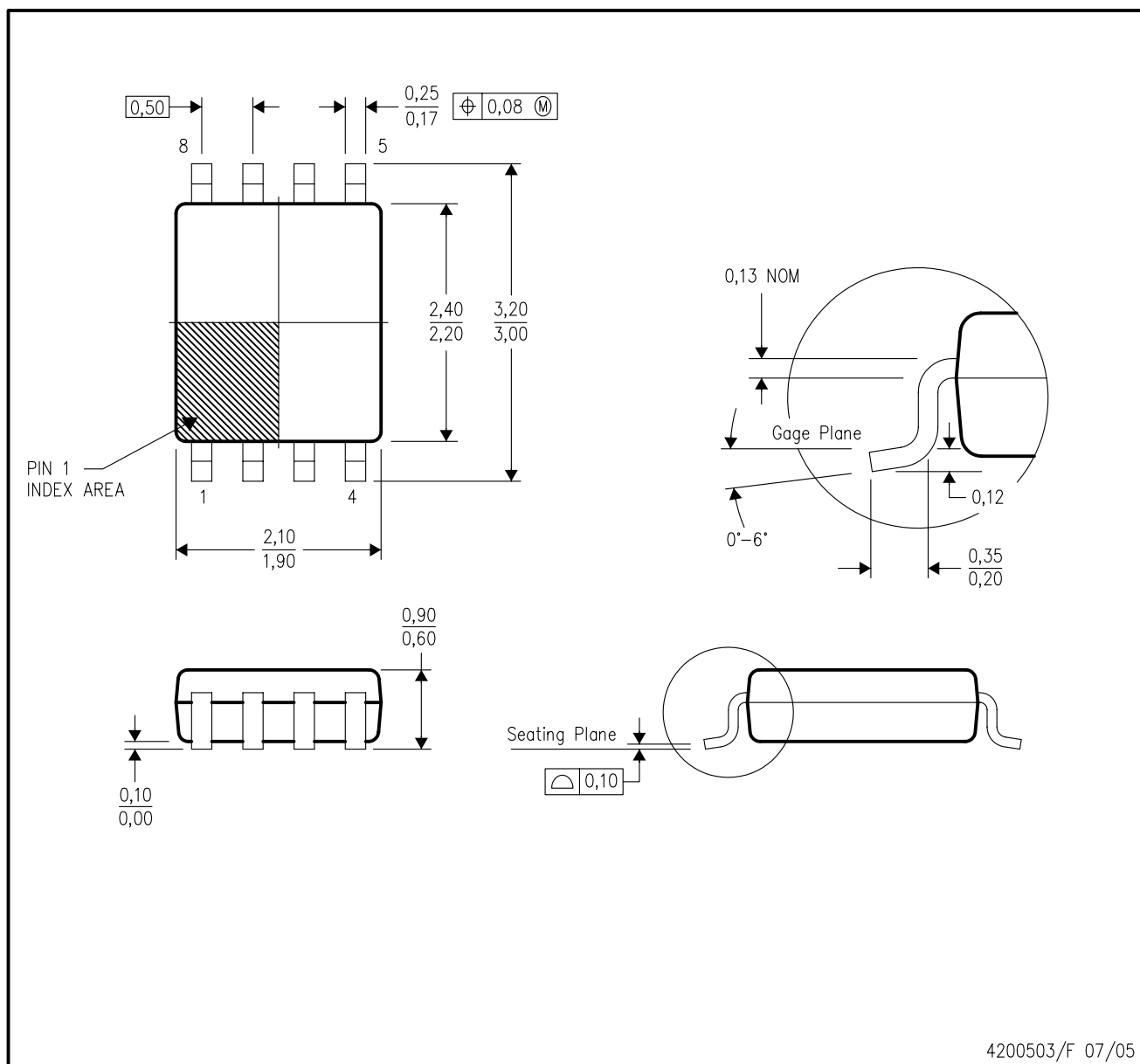
(6) Lead finish/Ball material - Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

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DCU (R-PDSO-G8)

PLASTIC SMALL-OUTLINE PACKAGE (DIE DOWN)



NOTES:

- All linear dimensions are in millimeters.
- This drawing is subject to change without notice.
- Body dimensions do not include mold flash or protrusion. Mold flash and protrusion shall not exceed 0.15 per side.
- Falls within JEDEC MO-187 variation CA.

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